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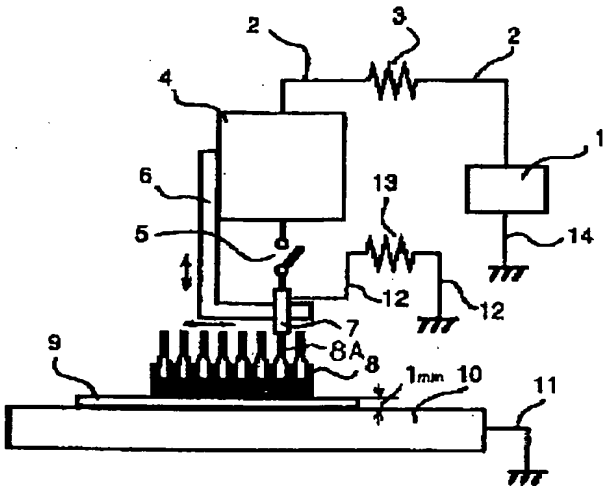
TITLE : ELECTROSTATIC BREAKDOWN TEST METHOD AND IMPLEMENTING DEVICE THEREOF



ABSTRACT : PURPOSE: To simulate a high-speed discharge phenomenon occurring when charged metal tools are brought into direct contact with a semiconductor device by setting the semiconductor device to be tested to the floating state apart from the ground potential, then conducting a test.

CONSTITUTION: A high-voltage capacitor formed between a metal body 4 and a grounding metal plate 10 is charged to high voltage from a power source 1 through a wiring 2 and a resistor 3 while a switch 5 is kept open. The switch 5 is closed, the high voltage of the metal body 4 is discharged to a semiconductor device 8, and an electrostatic breakdown test is conducted. The device 8 is separated from the ground potential by a capacity forming insulating sheet 9 in the floating state, a test terminal 8A is fixed at the ground potential in advance, then the metal body 4 is brought into contact with the terminal 8A for a test. No wiring is required between the metal body (conductor) 4 and the metal plate 10 (ground), the inductance of a test circuit can be reduced, and a high-speed discharge current can be fed to the device 8.